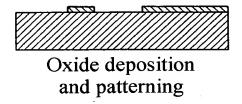
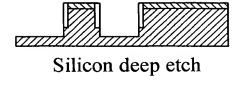
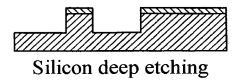


FIG. 1 (Prior Art)

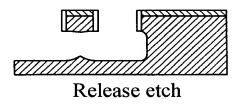
Political 3

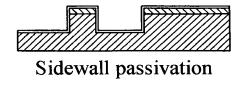












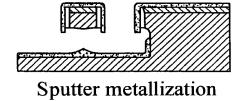




FIG. 2 (Prior Art)

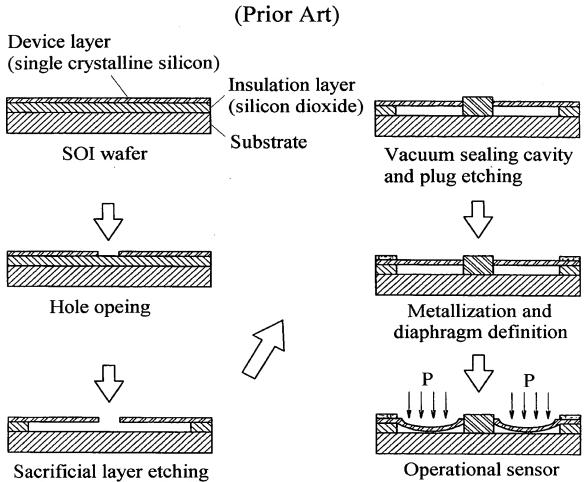
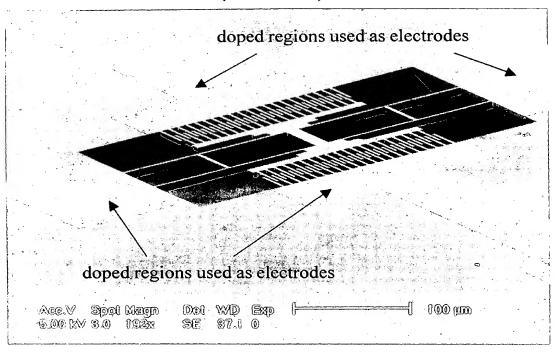




FIG. 3 (Prior Art)



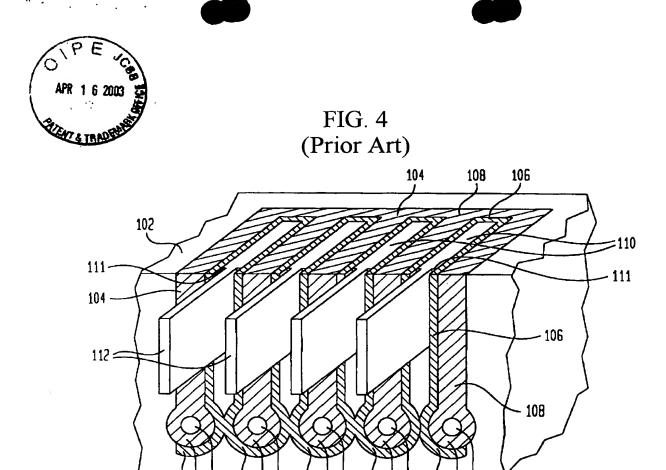
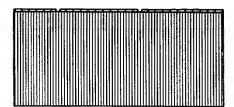
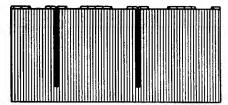




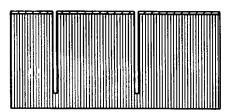
FIG. 5 (Prior Art)



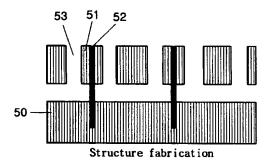
First etch mask deposition and patterning

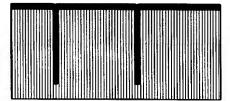


Second etch mask deposition and patterning



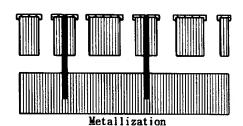
Deep silicon etching to form trenches

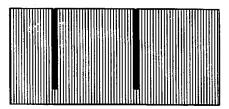




Trench filling by oxidation







Top oxide removal



FIG. 7A

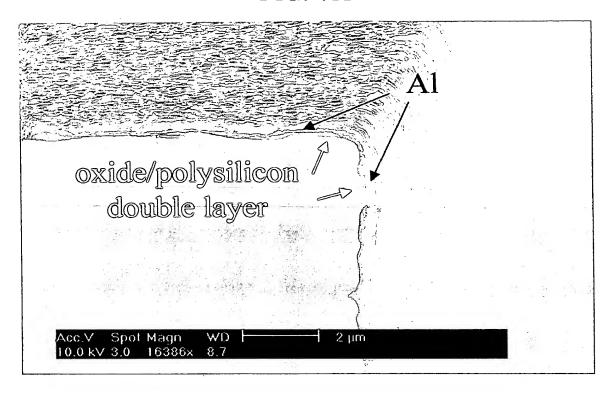




FIG. 7B

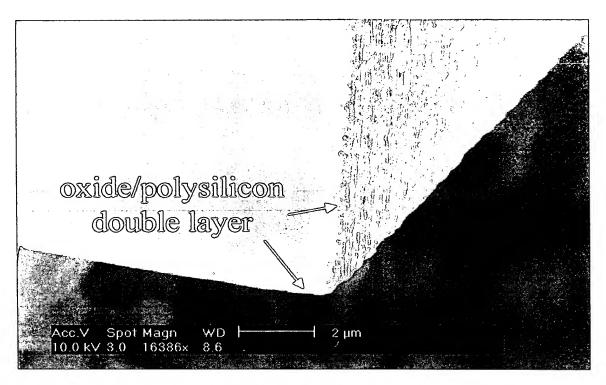




FIG. 9

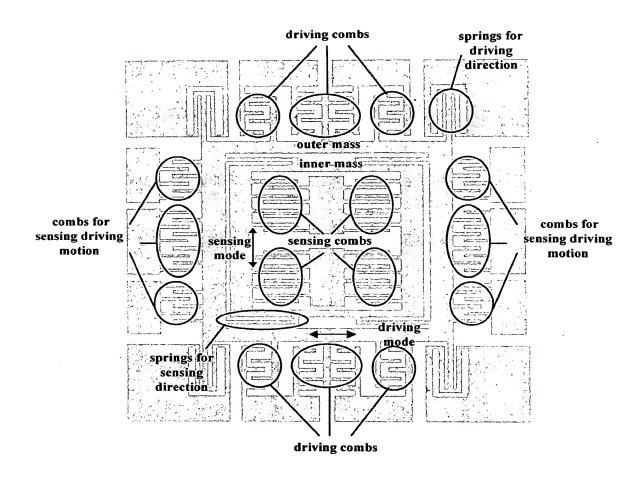






FIG. 12A

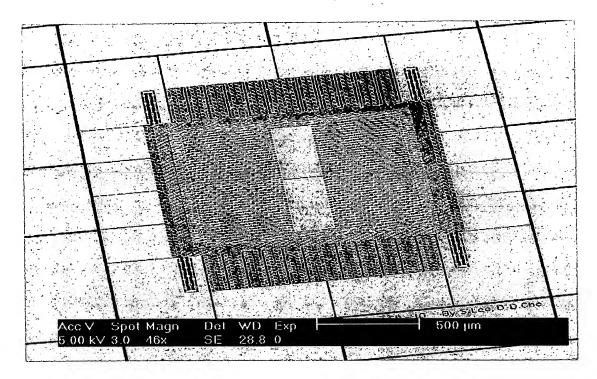
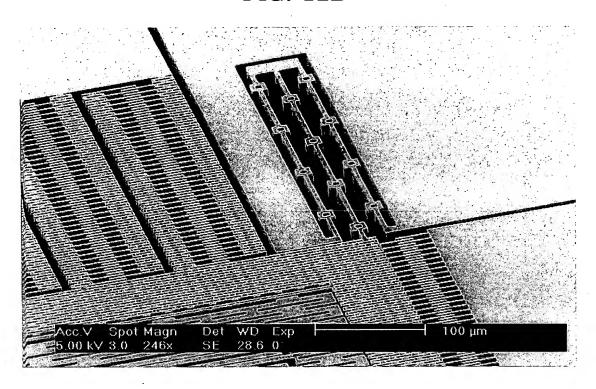




FIG. 12B





## FIG. 12C

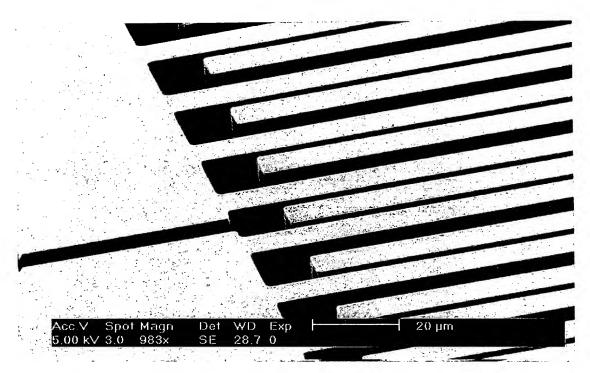




FIG. 12D

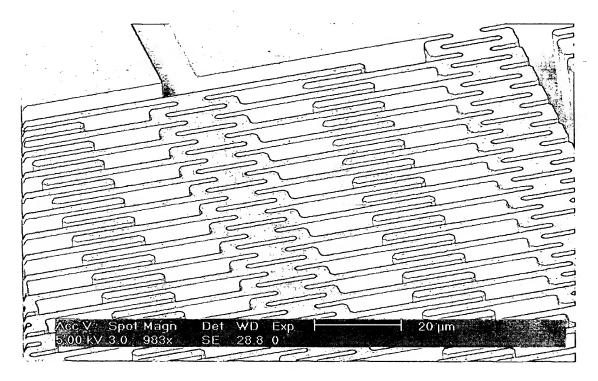
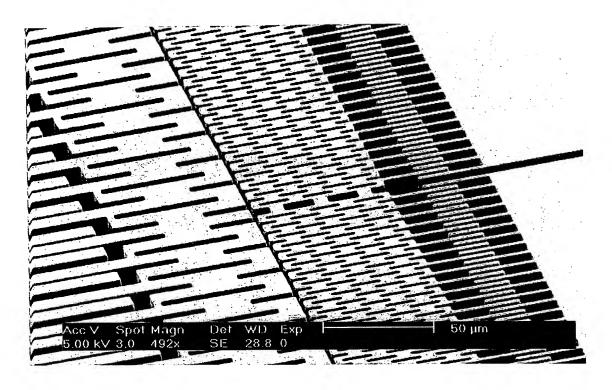




FIG. 12E





## FIG. 13

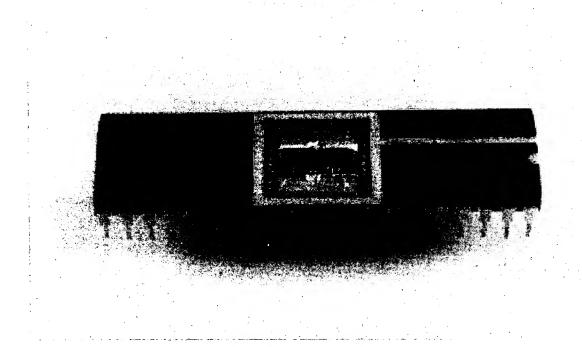




FIG. 14

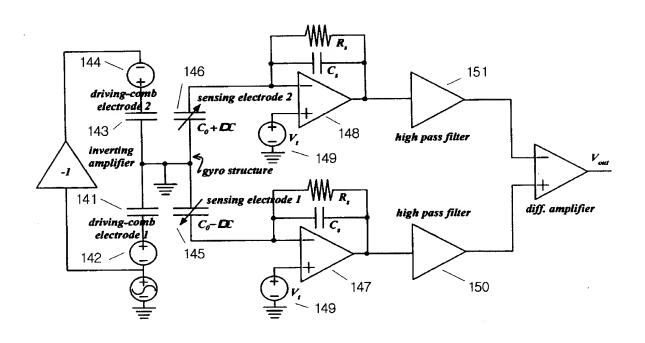
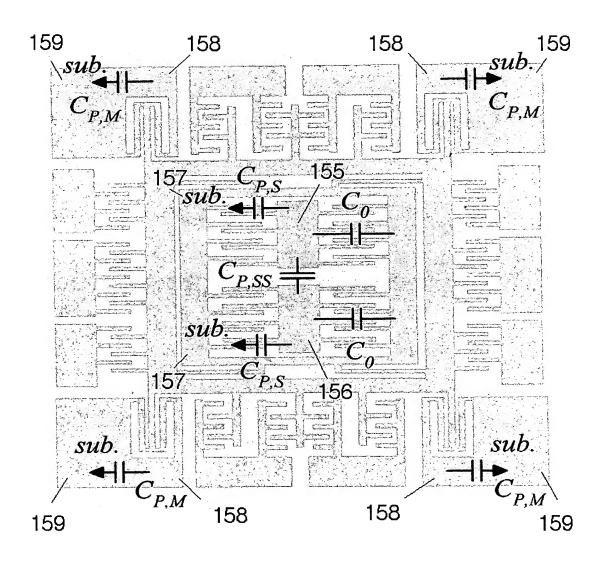


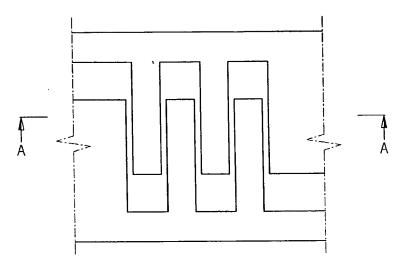


FIG. 15A





[Fig. 20]



[Fig. 21]

